

# 2SC4452

T-35-09

2059

NPN Epitaxial Planar Silicon Transistor

## High-Speed Switching Applications

©2811

### Features

- Fast switching speed
- Low collector saturation voltage
- High gain-bandwidth product
- Small collector capacity
- Very small-sized package permitting the 2SC4452-applied sets to be made small and slim

### Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V <sub>CB0</sub>	40	V
Collector to Emitter Voltage	V <sub>CES</sub>	40	V
Collector to Emitter Voltage	V <sub>CEO</sub>	15	V
Emitter to Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	200	mA
Peak Collector Current	i <sub>cp</sub>	500	mA
Base Current	I <sub>B</sub>	40	mA
Collector Dissipation	P <sub>C</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

### Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = 20V, I <sub>E</sub> = 0			0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> = 0			0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 10mA	*50	90	*200	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10mA	450	750		MHz
Collector Capacitance	c <sub>ob</sub>	V <sub>CB</sub> = 5V, f = 1MHz		1.4	4.0	pF
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA	0.13	0.25		V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA	0.80	0.85		V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	40			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	15			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	5			V
Turn-ON Time	t <sub>on</sub>	See specified Test Circuit.		8.0		ns
Storage Time	t <sub>stg</sub>		6.0		ns	
Turn-OFF Time	t <sub>off</sub>		12		ns	

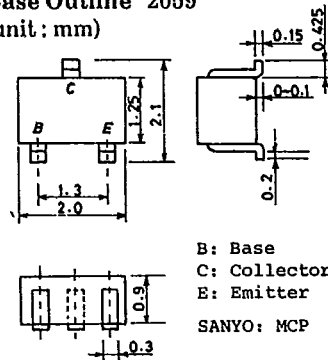
\*: The 2SC4452 is classified by 10mA h<sub>FE</sub> as follows:

50	2	100	70	3	140	100	4	200
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Marking: ST

h<sub>FE</sub> rank: 2,3,4

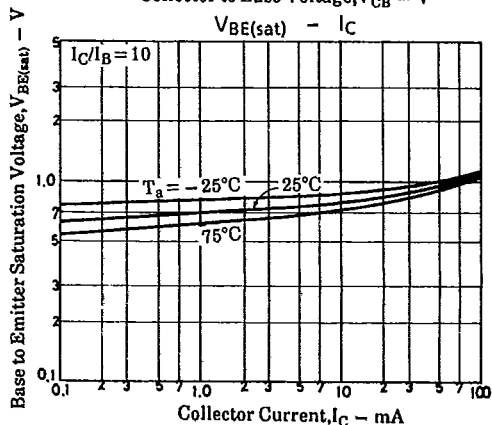
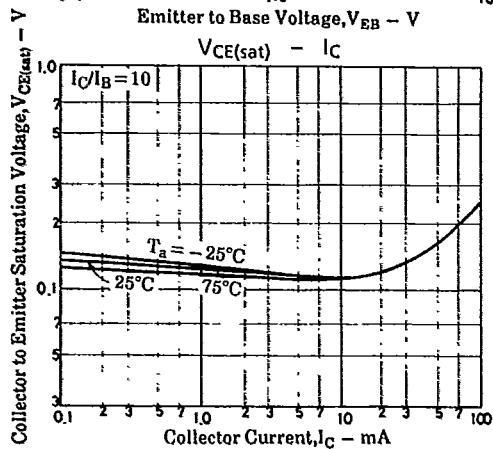
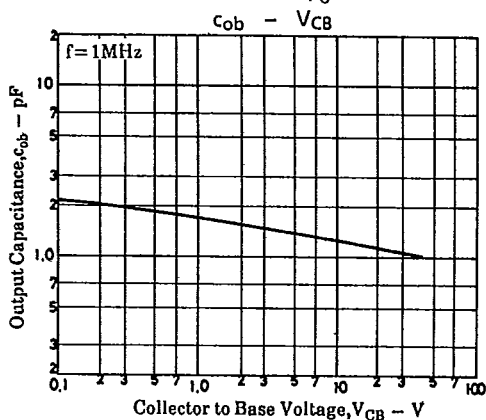
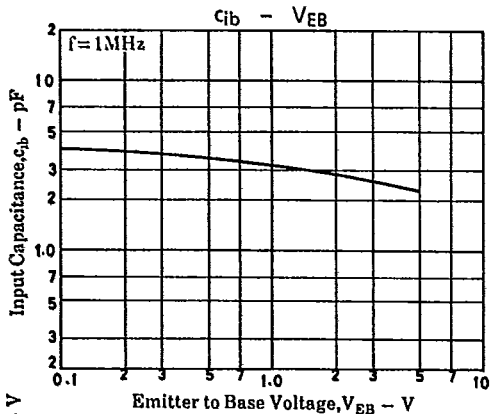
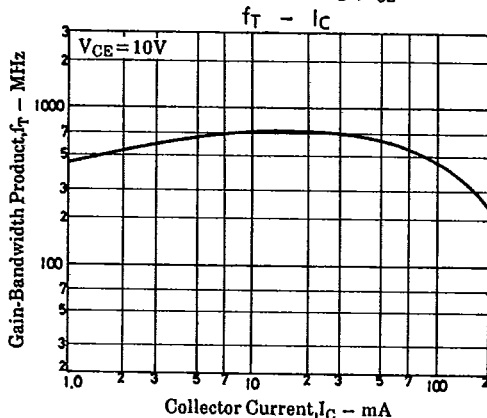
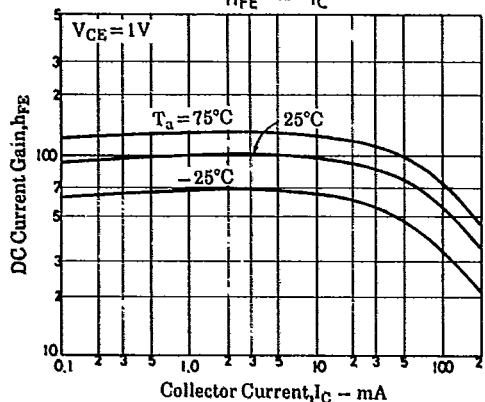
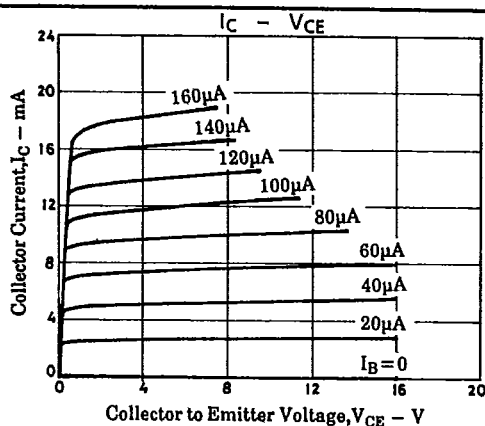
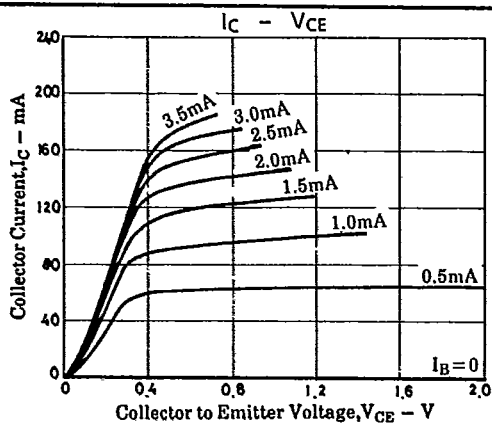
### Case Outline 2059 (unit: mm)



O278MO, TS No.2811-1/3

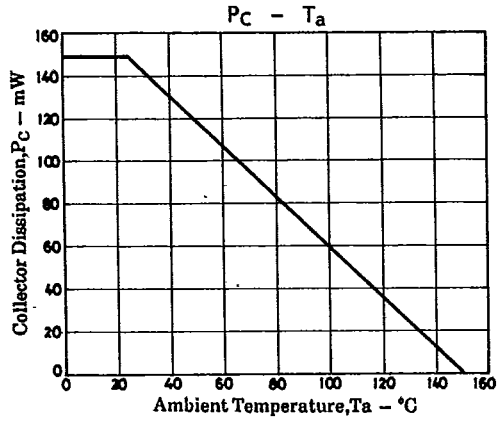
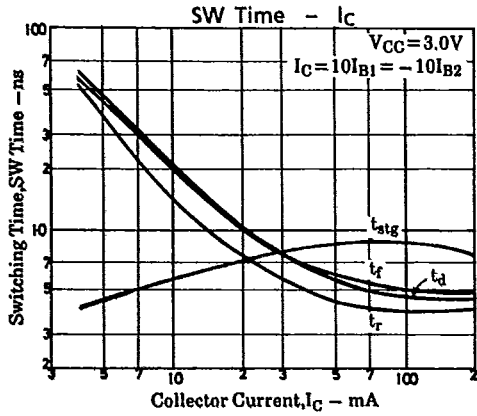
2SC4452

T-35-09

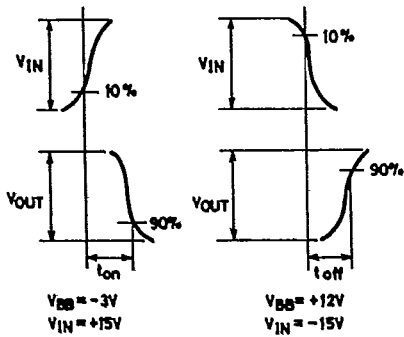
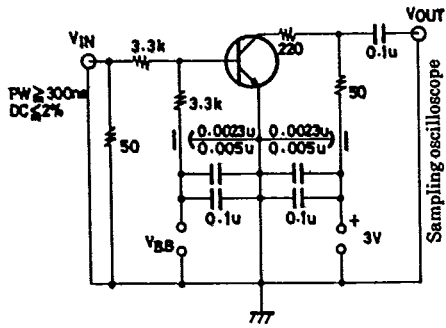


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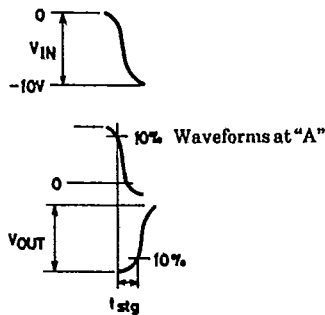
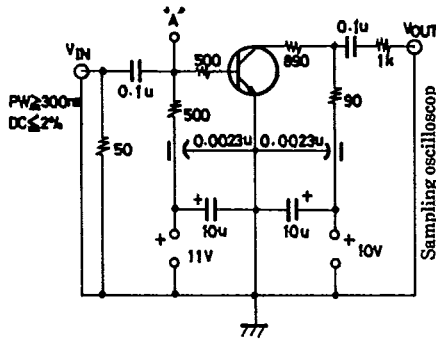
T-35-09



$t_{on}, t_{off}$  Test Circuit



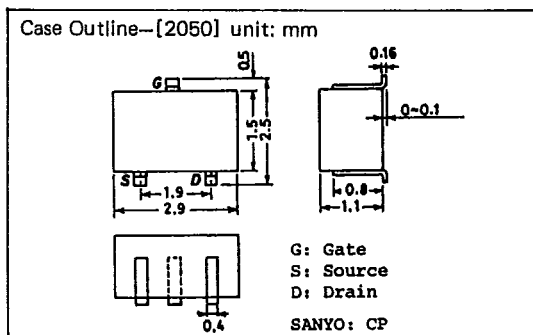
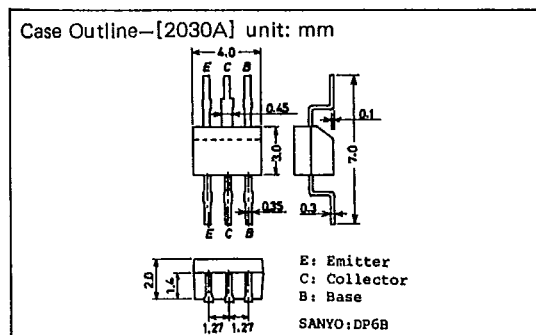
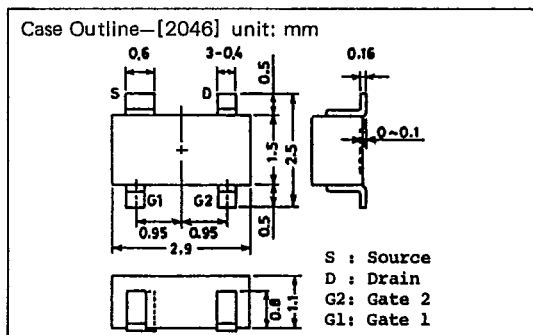
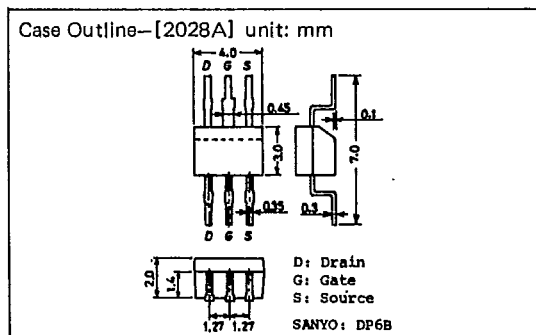
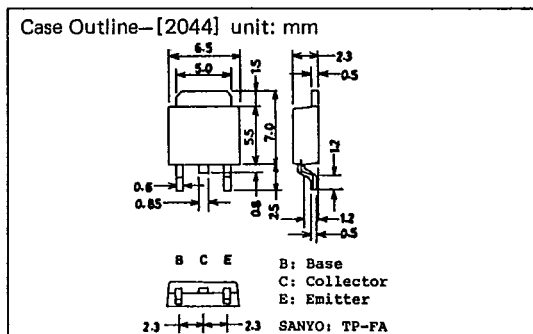
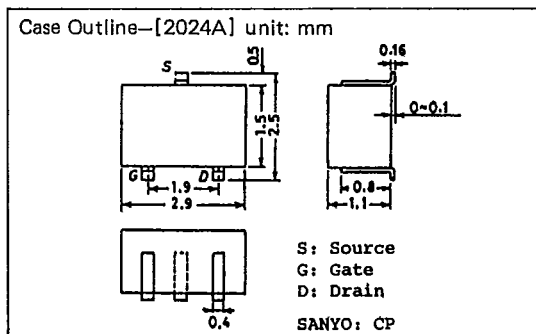
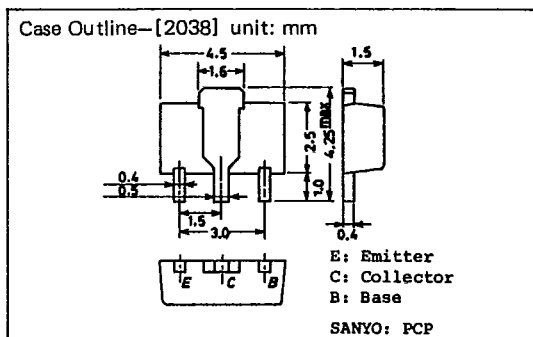
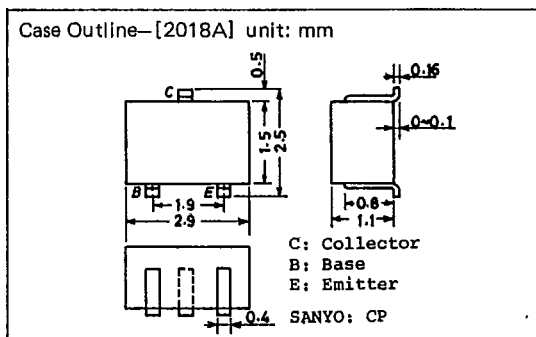
$t_{stg}$  Test Circuit



T-91-20

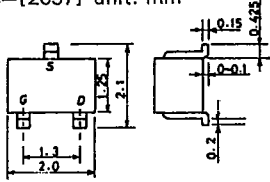
# CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.



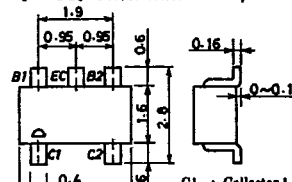
T-91-20

Case Outline—[2057] unit: mm



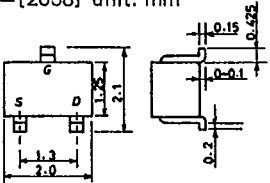
S: Source  
G: Gate  
D: Drain  
SANYO: MCP

Case Outline—[2066] unit: mm



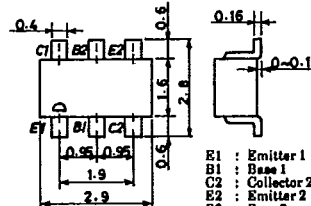
C1 : Collector 1  
C2 : Collector 2  
B2 : Base 2  
EC : Emitter Common  
B1 : Base 1  
SANYO : CP6

Case Outline—[2058] unit: mm



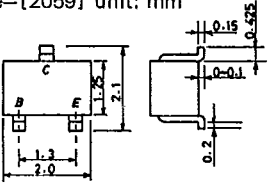
G: Gate  
S: Source  
D: Drain  
SANYO: MCP

Case Outline—[2067] unit: mm



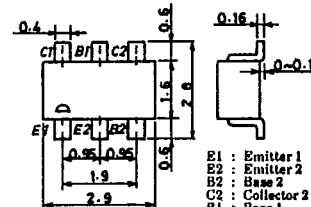
E1 : Emitter 1  
B1 : Base 1  
C2 : Collector 2  
E2 : Emitter 2  
B2 : Base 2  
C1 : Collector 1  
SANYO : CP6

Case Outline—[2059] unit: mm



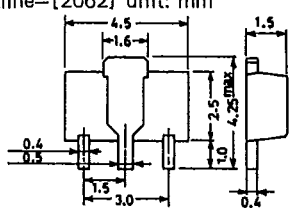
B: Base  
C: Collector  
E: Emitter  
SANYO: MCP

Case Outline—[2068] unit: mm



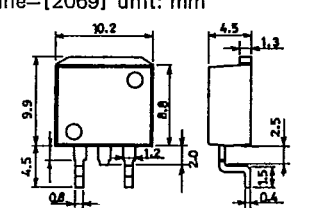
E1 : Emitter 1  
E2 : Emitter 2  
B2 : Base 2  
C2 : Collector 2  
B1 : Base 1  
C1 : Collector 1  
SANYO : CP6

Case Outline—[2062] unit: mm



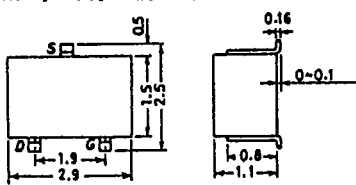
S: Source  
D: Drain  
G: Gate  
SANYO: PCP

Case Outline—[2069] unit: mm



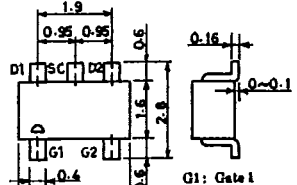
B: Base  
C: Collector  
E: Emitter  
SANYO: SMP

Case Outline—[2065] unit: mm



S: Source  
D: Drain  
G: Gate  
SANYO: CP

Case Outline—[2070] unit: mm



G1 : Gate 1  
G2 : Gate 2  
D2 : Drain 2  
SC : Source Common  
D1 : Drain 1  
SANYO : CP6

T-9120

